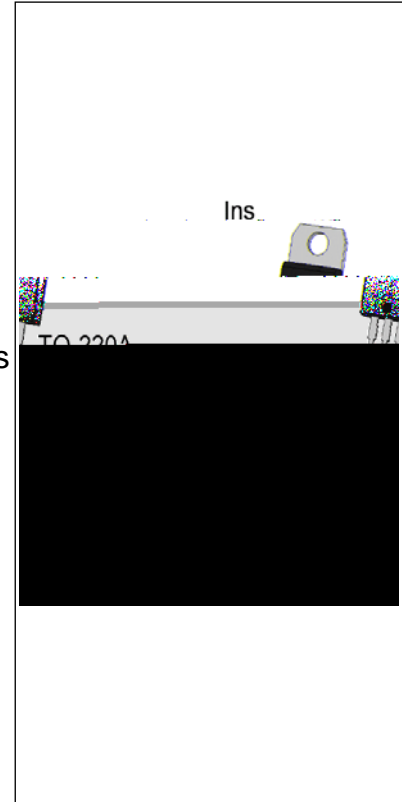


JST06A-800BW 6A TRIAC

Rev.A.1.1

DESCRIPTION:

The JST06A-800BW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST06A-800BW snubberless triac is especially recommended for use on inductive loads. By using an internal ceramic pad, JST06A-800BW provides a rated insulation voltage of 2500 VRMS, complying with UL standards (File ref: E252906). Package TO-220A is RoHS compliant.


MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	6	A
V_{DRM}/V_{RRM}	800	V
$I_{GT} / /$	50/50/50	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}		
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}		
RMS on-state current ($T_c = 100^\circ\text{C}$)	$I_{T(RMS)}$		
Non repetitive surge peak on-state current (full cycle, $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	65	
Non repetitive surge peak on-state current (full cycle, $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		72	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	21	s^2
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	di/dt	100	A/ μs
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$)	I_{GM}	4	A
Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	0.5	W

Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive,off-state;FIG.7)	V_{pp}	4	kV

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33$	- -	MAX.	50	mA
V_{GT}		- -	MAX.	1	V
V_{GD}		- -			

V V

=3

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ORDERING INFORMATION

J	ST	06	A	-800	BW
JieJie Microelectronics Co., Ltd.	Triacs	$I_{T(RMS)}:6A$	A:TO-220A(Ins)	800:V _{DRM} /V _{RRM} 800V	BW:IGT1-3 50mA

MARKING



FIG.1: Maximum power dissipation versus RMS on-state current

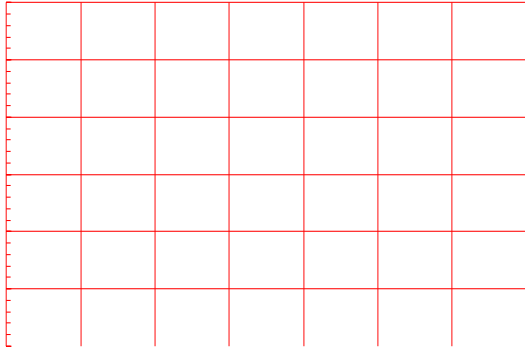
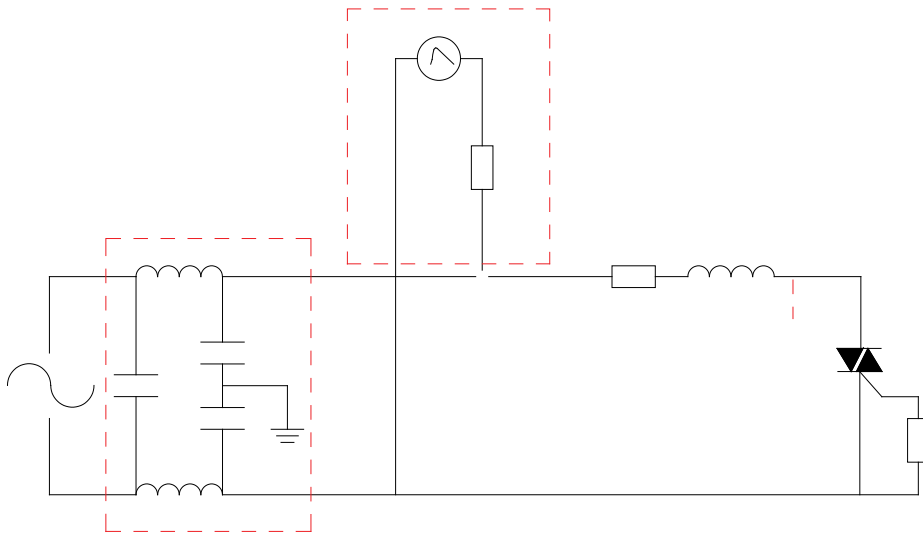


FIG.2: RMS on-state current versus case temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



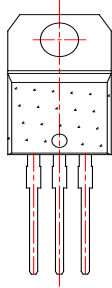
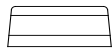
ORDERING INFORMATION

Order code	Voltage V _{DRM} /V _{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
JST06A-800BW	800	50	TO-220A(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Apr.11, 2023	A.1.0	Last updated
Oct.11, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

PACKAGE MECHANICAL DATA



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